

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 241998US2S		SERIAL NO. 10/649, New Application 704	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yoshiaki FUKUZUMI			
				FILING DATE Herewith		GROUP 2818	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	S					
	AB						
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	AD						
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	AH						
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	AJ						
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	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO	S					
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
TH	AW	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", 2000 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, pgs. 128-129					
TH	AX	Masashige SATO, et al., "Spin-Valve-Like Properties of Ferromagnetic Tunnel Junctions", Jpn. J. Appl. Phys. Vol. 36 (1997) pp. L200-L201					
	AY						
	AZ						<input type="checkbox"/> Additional References sheet(s) attached
Examiner TH-TH-10					Date Considered Sept 2004		
<small>*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							